

## Silicon PNP Power Transistors

## 2N5954 2N5955 2N5956

## DESCRIPTION

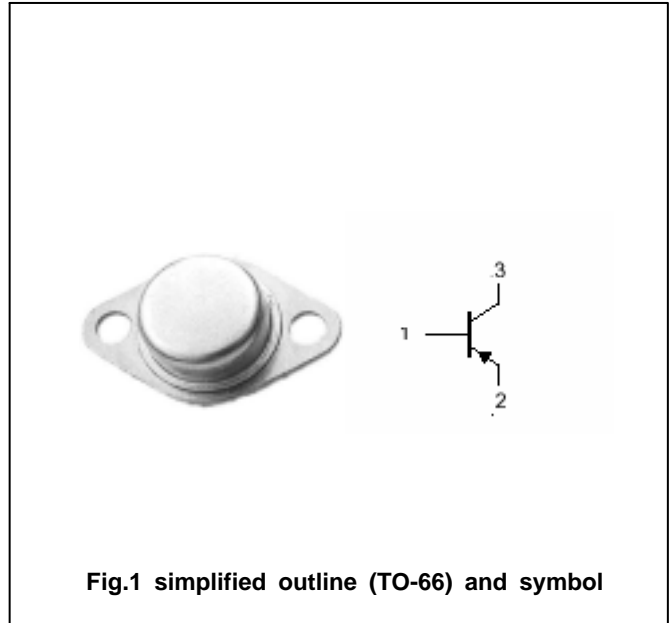
- With TO-66 package
- Low collector saturation voltage
- Excellent safe operating area
- Complement to type 2N6372/6373/6374

## APPLICATIONS

- Designed for driver circuits, switching and amplifier applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings( $T_a =$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	2N5954	-90	V
		2N5955	-70	
		2N5956	-50	
$V_{CEO}$	Collector-emitter voltage	2N5954	-80	V
		2N5955	-60	
		2N5956	-40	
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-6	A
$I_B$	Base current		-2	A
$P_D$	Total Power Dissipation	$T_C = 25$	40	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-65~200	

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	4.3	/W

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	2N5954	I <sub>C</sub> =-0.1A ; I <sub>B</sub> =0	-80			V
		2N5955		-60			
		2N5956		-40			
V <sub>CEsat</sub>	Collector-emitter saturation voltage	2N5954	I <sub>C</sub> =-2A; I <sub>B</sub> =-0.2A			-1.0	V
		2N5955	I <sub>C</sub> =-2.5A; I <sub>B</sub> =-0.25A				
		2N5956	I <sub>C</sub> =-3A; I <sub>B</sub> =-0.3A				
V <sub>BE-1</sub>	Base-emitter on voltage	2N5954	I <sub>C</sub> =-2A ; V <sub>CE</sub> =-4V			-2.0	V
		2N5955	I <sub>C</sub> =-2.5A ; V <sub>CE</sub> =-4V				
		2N5956	I <sub>C</sub> =-3A ; V <sub>CE</sub> =-4V				
V <sub>BE-2</sub>	Base-emitter on voltage		I <sub>C</sub> =-6A ; V <sub>CE</sub> =-4V			-3.0	V
I <sub>CEO</sub>	Collector cut-off current	2N5954	V <sub>CE</sub> =-65V; I <sub>B</sub> =0			-1.0	mA
		2N5955	V <sub>CE</sub> =-45V; I <sub>B</sub> =0				
		2N5956	V <sub>CE</sub> =-25V; I <sub>B</sub> =0				
I <sub>CEV</sub>	Collector cut-off current(R <sub>BE</sub> =100 )		V <sub>CE</sub> =Rated V <sub>CE</sub> ; V <sub>BE(off)</sub> =1.5V T <sub>C</sub> =150			-0.1 -2.0	mA
I <sub>EBO</sub>	Emitter cut-off current		V <sub>EB</sub> =-5V; I <sub>C</sub> =0			-0.1	mA
h <sub>FE-1</sub>	DC current gain	2N5954	I <sub>C</sub> =-2A ; V <sub>CE</sub> =-4V	20		100	
		2N5955	I <sub>C</sub> =-2.5A ; V <sub>CE</sub> =-4V				
		2N5956	I <sub>C</sub> =-3A ; V <sub>CE</sub> =-4V				
h <sub>FE-2</sub>	DC current gain		I <sub>C</sub> =-6A ; V <sub>CE</sub> =-4V	5			
f <sub>T</sub>	Transition frequency		I <sub>C</sub> =-1A;V <sub>CE</sub> =-4V;f=1.0MHz	5			MHz

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PACKAGE OUTLINE

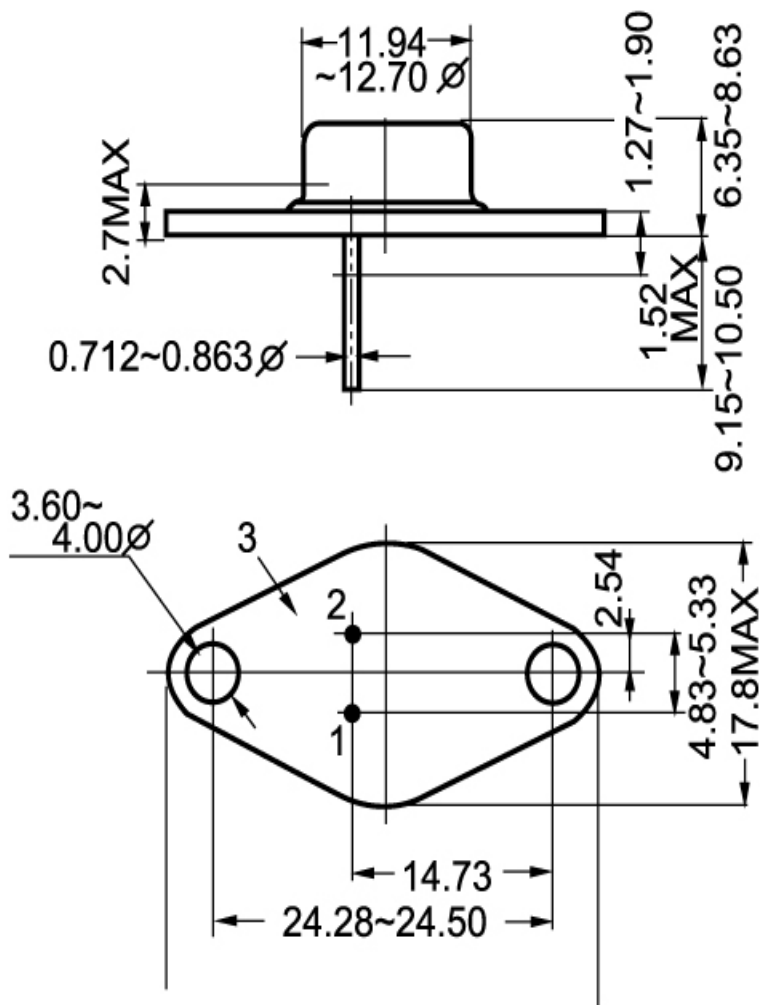


Fig.2 outline dimensions